

Amendments to the Specification:

Please replace the paragraph beginning on page 3, line 29 with the following amended paragraph:

Also included in diode 200 is a heavily N⁺ doped source region 205, which provides a channel stop for improved reliability, and a field oxide layer 206. As shown in FIG. 2, the N⁺ doped source region 205 is disposed in the N⁻ doped epitaxial layer 203, thereby laterally spacing the N⁺ doped source region 205 from the P⁺ doped region 201 and P⁻ doped well 202. As shown by comparison of FIGS. 1 and 2, the electrical field, represented by the arrows E, is substantially more dispersed at the corner of the pn junction of diode 200 of the present invention compared with prior art diode 100.